

ALLRESIST develops, manufactures, and distributes resists for optical and electron beam lithography, as well as process chemicals used in the fabrication of electronic components.

- Broad product portfolio – resists for (nearly) all standard technologies
- Customized, process-optimized resists developed to meet specific industrial requirements – a globally unique service
- Innovative products tailored for new applications and advanced technologies with harmless and environmentally friendly properties
- Strong focus on industrial research, with collaborative projects involving research institutions and industry partners
- Individual, competent product- and technology consulting
- Short delivery times, in-stock products available for immediate delivery
- Customer-friendly packing with container sizes from 250 ml, test samples are available



Due to its expertise and high flexibility, ALLRESIST incorporates specific customer requirements right from the conception and development stages of new resists.

We also offer adhesion promoters, thinners, developers, stoppers and removers as complimentary process chemicals optimized for our resists.

Visit our website at www.allresist.com for detailed product information, the Resist Wiki, AR NEWS, FAQs, and safety data sheets.



ALLRESIST is an innovative, family-run company founded in 1992 by Brigitte and Matthias Schirmer. Their daughter, Ulrike Schirmer, is now taking over the reins and aims to lead and further develop the company guided by the same core values.

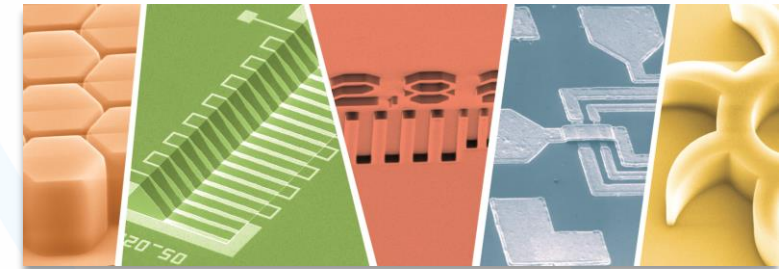
Quality Innovation Competence
Creativity Sustainability
Customer orientation Fairness
Social and ecological responsibility

Most important prizes and awards:

- Ludwig Erhard Prize
- Quality Award Berlin-Brandenburg
- Innovation Award Brandenburg
- Germany's Customer Champions
- Germany's Employee Champions
- Excellent Knowledge Organization
- Technology Transfer Prize Brandenburg
- Future Award East Brandenburg
- Brigitte Schirmer – Entrepreneur of the State of Brandenburg
- Brigitte and Matthias Schirmer – Order of Merit of Brandenburg



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**Your specialist for
 resists and process chemicals
 for over 30 years**



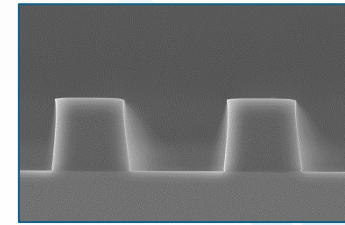
Resist product overview

From our 2025 price list – Custom-made products available upon request, tailored to your specific production process!

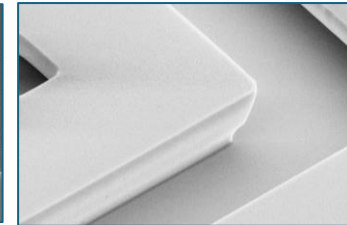
Application	Product	Do [μm] / 4000 rpm	
Positive photoresists, i-line, g-line	Spray photoresists for various applications	AR-P 1210, 1220	[0.5 - 10]
	Photoresists for mask production; fine gradation, high resolution	AR-P 3110, 3120, 3170	1.0 ; 0.6 ; 0.1
	Thick-layer photoresists; multiple coating up to 100 μm	AR-P 3210, 3220, 3250	10 ; 10 ; 5
	Standard photoresists; wide process window, high resolution	AR-P 3510 (T), 3540 (T)	2.0 ; 1.4
	High-contrast photoresist for sub-μm resolution	AR-P 3740	1.4
	Photoresist for undercut structures (single-layer lift-off)	AR-P 5350	1.0
	Thermally stable photoresist up to 300 °C	SX AR-P 3500/8	1.4
Negative photoresists	Spray photoresists for various applications	AR-N 2210, 2220	[0.5 - 10]
	Standard photoresist for i-line, g-line, and lift-off; highly sensitive, high-resolution	AR-N 4340	1.4
	Resists for i- and g-line; high layer thickness, easy removal, steep edge profiles, excellent resolution, lift-off	CAR 44: AR-N 4400-50, 4400-25, 4400-10, 4400-05	50 ; 25 ; 10 ; 5 (1000 rpm)
	Resists for stable structures up to 100 μm; SU-8 equivalent	Atlas 46: AR-N 4600-10	10 (1000 rpm)
	Thermally stable photoresist up to 300 °C for 1- and 2-layer systems	SX AR-N 4340/7	1.4
Special systems	KOH-etch-stable protective coating (up to 40 % KOH)	AR-PC 5040	2.8
	Protective coating; wafer backside protection, resistant to 40 % KOH and 38 % HF	SX AR-PC 5000/41	5
	Conductive protective coating for e-beam resists (except Medusa 84)	Electra 92: AR-PC 5092.02	0.04
	New: Conductive coating allrounder for e-beam resists (except CAR)	Electra 94: AR-PC 5094.02	0.04
	Bottom resist for two-layer lift-off systems (pos./neg. photoresist)	AR-BR 5640, 5480	1.0 ; 0.5
	Thermally structurable resist; highest resolution with NanoFrazor	Phoenix 81: PPA polymer for AR-P 8100	0.02 ... 0.2
Positive e-beam resists	E-beam resist copolymer PMMA/MA 33 %; ultra-high resolution	AR-P 617.03, 617.06, 617.08, 617.14	0.09 ... 1.75
	E-beam resists PMMA 50K, 200K, 600K, 950K; ultra-high resolution. Available in chlorobenzene (1), anisole (2), ethyl lactate (9)	AR-P 641-671, 632-672, 639-679	0.03 ... 1.87
	E-beam resists; high-resolution, highly sensitive, highly plasma-etch resistant, process-stable	CSAR 62: AR-P 6200.04, 6200.09, 6200.13, 6200.18	0.08 ... 0.80
	E-beam resist for high PMMA layers up to 100 μm; also deep UV	AR-P 6510.15	45 (200 rpm)
Negative e-beam resists	Mix & match; etch-resistant, high-resolution, ultra-sensitivity	AR-N 7520.07, 7520.11, 7520.17 new	0.4 ; 0.2 ; 0.1
	Mix & match; etch-resistant, high-resolution, high-precision edges	AR-N 7520.073, 7520.18	0.4 ; 0.1
	New: E-beam resists with improved HSQ polymer; high process and storage stability, high etch-stability, strong adhesion	Medusa 84 SiH: SX AR-N 8400.04, 8400.08, 8400.12, 8400.22	0.05 ; 0.10 ; 0.2 ; 0.4



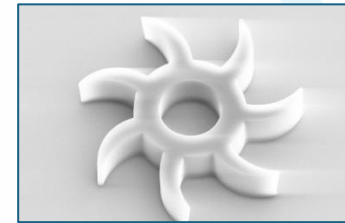
**Innovation
Creativity
Customer-specific solutions**



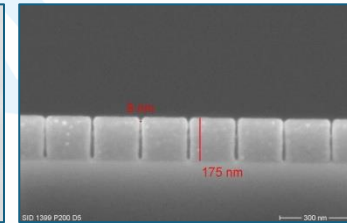
20 μm high bars with AR-P 3220



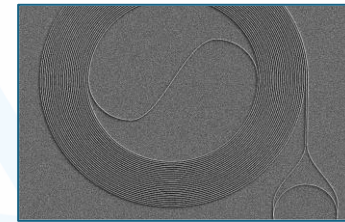
Lift-off structure with 2-Layer of AR-P 617



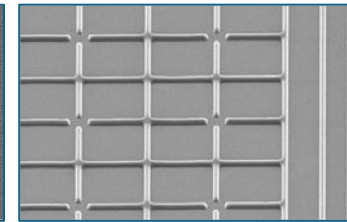
Turbine wheel 500 μm with AR-N 4400-50



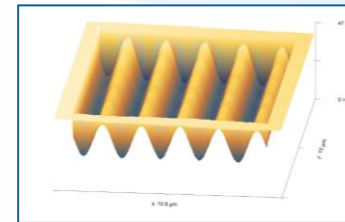
10 nm trenches with AR-P 6200.09



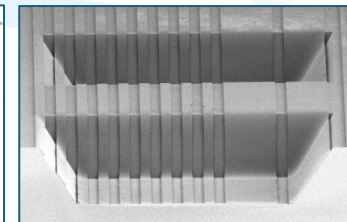
100 nm structures with Medusa 84



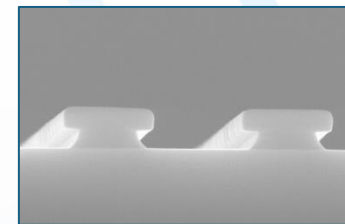
400 nm bars with AR-N 7520.073



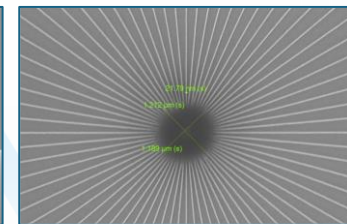
Sinusoidal structures etched into silicon - Phoenix 81 using NanoFrazor



AR-N 2220 Resist structures in 200 μm deep etch pits



Thermally stable two-layer lift-off system with AR-BR 5460 and SX AR-N 4340/7



Medusa 84 Siemens star on glass, processed with Electra 94